





#### **60V PNP MEDIUM POWER TRANSISTOR IN SOT223**

#### **Features**

- BV<sub>CEO</sub> > -60V
- I<sub>C</sub> = -1A High Continuous Current
- Low Saturation Voltage  $V_{CE(sat)} < -600 mV @ -1A$
- Complementary NPN Type: FZT491
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208@3
- Weight: 0.112 grams (Approximate)

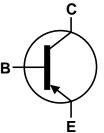
### **Applications**

- Power MOSFET & IGBT Gate Driving
- Low Loss Power Switching

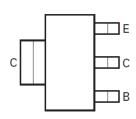




Top View



Device Symbol



Top View Pin-Out

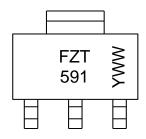
### Ordering Information (Note 4)

	Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
	FZT591TA	FZT591	7	12	1,000	
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.						

- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

SOT223



FZT 591 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W = \text{Week Code } (01~53)$ 

Downloaded from **Arrow.com**.





### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-80	V
Collector-Emitter Voltage	$V_{\sf CEO}$	-60	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current	lc	-1	Α
Peak Pulse Current	I <sub>CM</sub>	-2	Α
Base Current	I <sub>B</sub>	-200	mA

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)	_ [	2.0	W	
Power Dissipation	(Note 7)	$P_D$	1.6		
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	62.5		]	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ heta JL}$	19.4		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

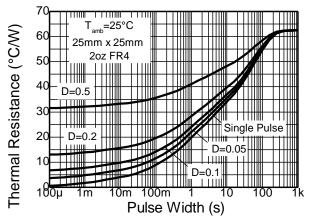
  6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 9. Same as Note 5, except the device is mounted on minimum recommended pad layout.

  9. Thermal resistance from junction to solder-point (at the end of the collector lead).

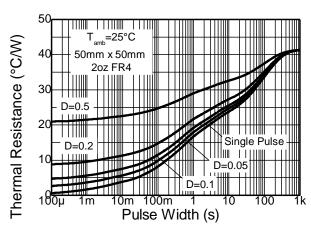
  10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



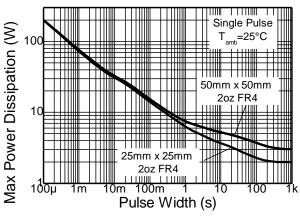
## **Thermal Characteristics and Derating Information**



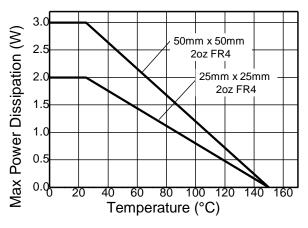
**Transient Thermal Impedance** 



**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



**Derating Curve** 





### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

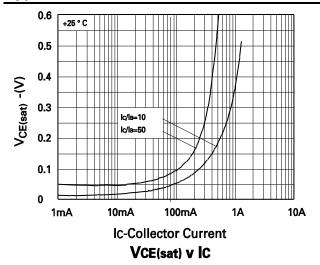
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-80	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CEO</sub>	-60	_	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	8.1	_	V	$I_E = -100 \mu A$
Collector Cut-Off Current	I <sub>CBO</sub>	_	<1	-100	nA	V <sub>CB</sub> = -60V
Collector Cut-Off Current	I <sub>CES</sub>	_	<1	-100	nA	V <sub>CES</sub> = -60V
Emitter Cut-Off Current	I <sub>EBO</sub>	-	<1	-100	nA	$V_{EB} = -5.6V$
Collector-Emitter Saturation Voltage (Note 11)	V <sub>CE(sat)</sub>	_ _	-175 -350	-300 -600	mV	$I_C = -500\text{mA}, I_B = -50\text{mA}$ $I_C = -1A, I_B = -100\text{mA}$
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	-	965	-1200	mV	$I_C = -1A$ , $I_B = -100mA$
Base-Emitter Turn-On Voltage (Note 11)	V <sub>BE(on)</sub>	_	830	-1000	mV	$I_C = -1A, V_{CE} = -5V$
DC Current Transfer Static Ratio (Note 11)	h <sub>FE</sub>	100 100 80 15	220 175 155 40	300 - -	-	$I_{C}$ = -1mA, $V_{CE}$ = -5V $I_{C}$ = -500mA, $V_{CE}$ = -5V $I_{C}$ = -1A, $V_{CE}$ = -5V $I_{C}$ = -2A, $V_{CE}$ = -5V
Transitional Frequency	f <sub>T</sub>	150	-	-	MHz	$V_{CE} = -10V, I_{C} = -50mA$ f = 100MHz
Output Capacitance	$C_{obo}$	=	=	10	pF	$V_{CB} = -10V. f = 1MHz$

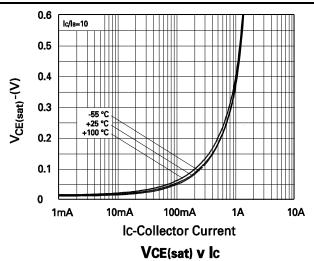
Note:

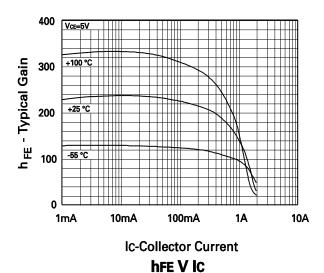
11. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

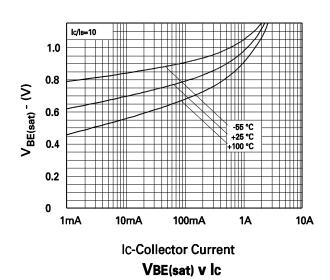


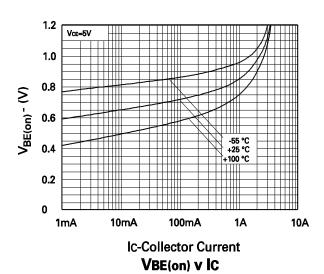
## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

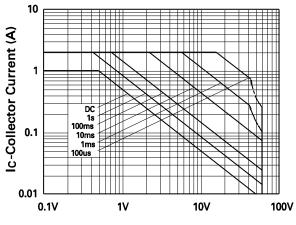












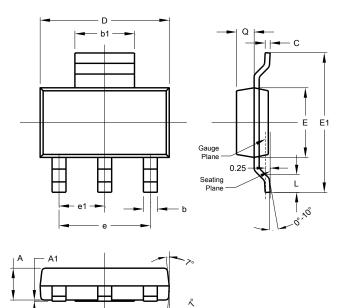
VCE - Collector Emitter Voltage (V)

Safe Operating Area



## **Package Outline Dimensions**

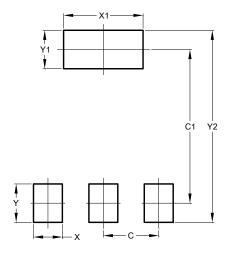
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00





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